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NCE N-Channel Enhancement Mode Power MOSFET

Description

The NCE0260P uses advanced trench technology and design to provide excellent RDS(ON) with low gate charge. It can be used in a wide variety of applications.

General Features

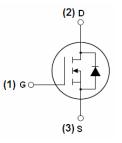
- V_{DS} =200V, I_{D} =60A $R_{DS(ON)}$ <32m Ω @ V_{GS} =10V
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

100% UIS TESTED!

100% ΔVds TESTED!



Schematic diagram



Marking and pin assignment



TO-3P top view

Package Marking and Ordering Information

| Device Marking | Device | Device Package | Reel Size | Tape width | Quantity |
|----------------|----------|----------------|-----------|------------|----------|
| NCE0260P | NCE0260P | TO-3P | - | - | - |

Absolute Maximum Ratings (T_C=25 ℃unless otherwise noted)

| Parameter | Symbol | Limit | Unit |
|--|-----------------------|------------|--------------|
| Drain-Source Voltage | V _{DS} | 200 | V |
| Gate-Source Voltage | V _{GS} | ±20 | V |
| Drain Current-Continuous | I _D | 60 | Α |
| Drain Current-Continuous(T _C =100 °C) | I _D (100℃) | 42 | Α |
| Pulsed Drain Current | I _{DM} | 280 | Α |
| Maximum Power Dissipation | P _D | 300 | W |
| Derating factor | | 2.0 | W/℃ |
| Single pulse avalanche energy (Note 5) | E _{AS} | 225 | mJ |
| Operating Junction and Storage Temperature Range | T_{J} , T_{STG} | -55 To 175 | $^{\circ}$ C |



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Thermal Characteristic

| Thermal Resistance, Junction-to-Case (Note 2) | $R_{	heta JC}$ | 0.5 | °C/W |
|---|----------------|-----|------|
|---|----------------|-----|------|

Electrical Characteristics (T_C=25 °C unless otherwise noted)

| Parameter | Symbol | Condition | Min | Тур | Max | Unit |
|------------------------------------|---------------------|--|---|------|------|------|
| Off Characteristics | • | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | V _{GS} =0V I _D =250μA | V _{GS} =0V I _D =250μA 200 | | - | V |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} =200V,V _{GS} =0V - | | - | 1 | μA |
| Gate-Body Leakage Current | I _{GSS} | V _{GS} =±20V,V _{DS} =0V | - | - | ±100 | nA |
| On Characteristics (Note 3) | | | | | | |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS}=V_{GS}$, $I_{D}=250\mu A$ | 2 | 3.2 | 4 | V |
| Drain-Source On-State Resistance | R _{DS(ON)} | V _{GS} =10V, I _D =20A | - | 24 | 32 | mΩ |
| Forward Transconductance | g FS | V _{DS} =5V,I _D =30A | 40 | - | - | S |
| Dynamic Characteristics (Note4) | | | | | | |
| Input Capacitance | C _{lss} | \/ -50\/\/ -0\/ | - | 6200 | - | PF |
| Output Capacitance | Coss | V_{DS} =50V, V_{GS} =0V, F=1.0MHz | - | 950 | - | PF |
| Reverse Transfer Capacitance | C _{rss} | F=1.0WHZ | - | 460 | - | PF |
| Switching Characteristics (Note 4) | | | | | | |
| Turn-on Delay Time | t _{d(on)} | | - | 33 | - | nS |
| Turn-on Rise Time | t _r | V_{DD} =100V, R_{L} =15 Ω | - | 20 | - | nS |
| Turn-Off Delay Time | t _{d(off)} | V_{GS} =10V, R_{G} =2.5 Ω | - | 21 | - | nS |
| Turn-Off Fall Time | t _f | | - | 31 | - | nS |
| Total Gate Charge | Q_g | \/ -100\/ -20 \ | - | 130 | | nC |
| Gate-Source Charge | Q _{gs} | V_{DS} =100V, I_{D} =30A, V_{GS} =10V | - | 36 | | nC |
| Gate-Drain Charge | Q_{gd} | V _{GS} =10V | - | 46 | | nC |
| Drain-Source Diode Characteristics | | | • | | | |
| Diode Forward Voltage (Note 3) | V _{SD} | V _{GS} =0V,I _S =30A | - | | 1.2 | V |
| Diode Forward Current (Note 2) | I _S | | - | - | 60 | Α |
| Reverse Recovery Time | t _{rr} | TJ = 25°C, IF = 30A | - | 42 | | nS |
| Reverse Recovery Charge | Qrr | di/dt = 100A/µs ^(Note3) - 66 | | | nC | |
| Forward Turn-On Time | t _{on} | Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD) | | | | |

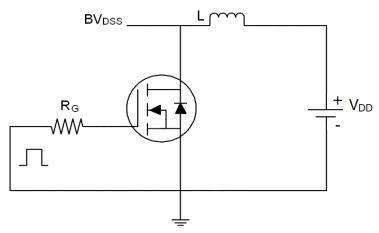
Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production
- 5. E_AS condition: j=25 $^{\circ}\text{C}\,\text{,V}_{DD}\text{=}50\text{V},\text{V}_{G}\text{=}10\text{V},\text{L=}0.5\text{mH,Rg=}25\Omega$

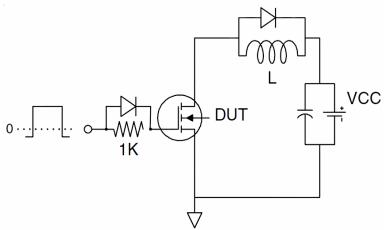
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Test Circuit

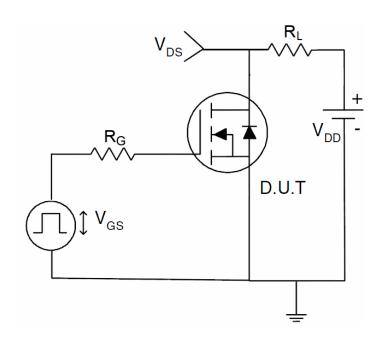
1) E_{AS} test Circuits



2) Gate charge test Circuit



3) Switch Time Test Circuit



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Typical Electrical and Thermal Characteristics (Curves)

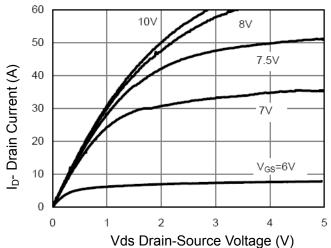


Figure 1 Output Characteristics

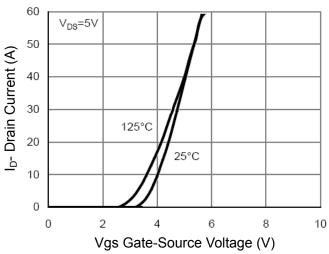


Figure 2 Transfer Characteristics

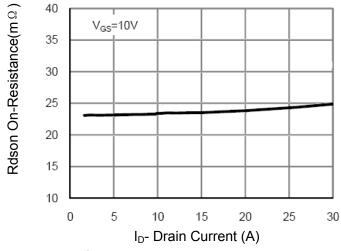


Figure 3 Rdson- Drain Current

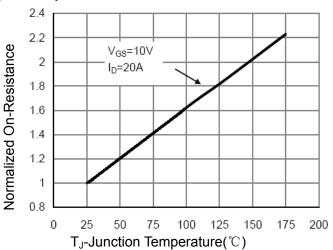


Figure 4 Rdson-Junction Temperature

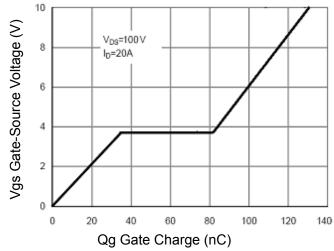


Figure 5 Gate Charge

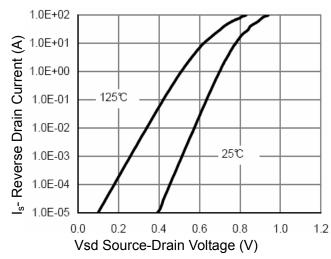


Figure 6 Source- Drain Diode Forward

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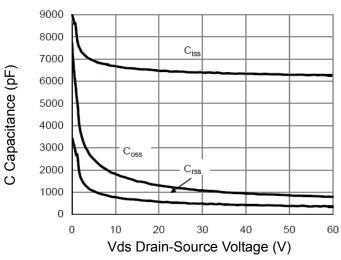


Figure 7 Capacitance vs Vds

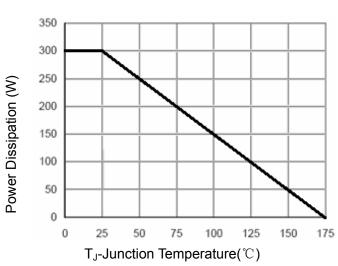


Figure 9 Power De-rating

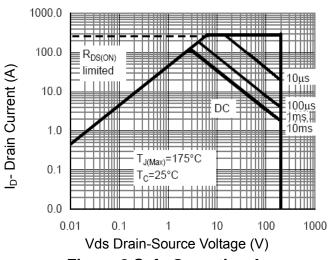


Figure 8 Safe Operation Area

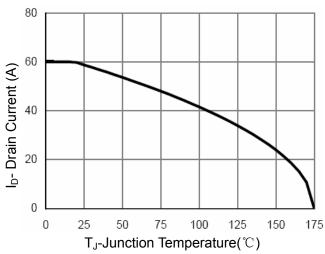


Figure 10 Current De-rating

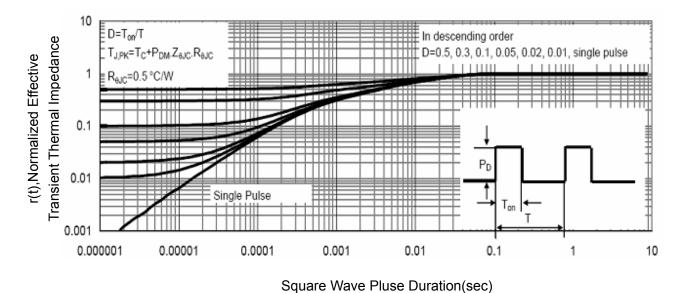
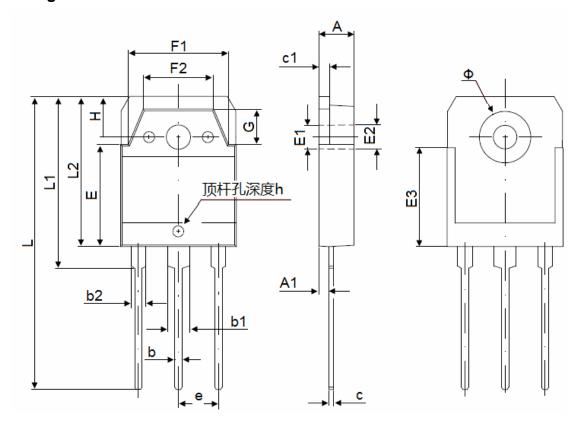


Figure 11 Normalized Maximum Transient Thermal Impedance



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TO-3P Package Information



| C m. h. a. l | Dimensions | In Millimeters | Dimensions In Inches | | |
|--------------|------------|----------------|----------------------|-------|--|
| Symbol | Min | Max | Min | Max | |
| А | 4.600 | 5.000 | 0.181 | 0.197 | |
| A 1 | 1.200 | 1.600 | 0.047 | 0.063 | |
| b | 0.800 | 1.200 | 0.031 | 0.047 | |
| b1 | 2.800 | 3.200 | 0.110 | 0.126 | |
| b2 | 1.800 | 2.200 | 0.071 | 0.087 | |
| С | 0.500 | 0.700 | 0.020 | 0.028 | |
| c 1 | 1.450 | 1.650 | 0.057 | 0.065 | |
| D | 15.450 | 15.850 | 0.606 | 0.622 | |
| Е | 13.700 | 14.100 | 0.539 | 0.555 | |
| E 1 | 3.200 | REF | 0.126 REF | | |
| E 2 | 3.300 | REF | 0.130 REF | | |
| E 3 | 13.45 | 0 REF | 0.530 REF | | |
| F 1 | 13.400 | 13.800 | 0.528 | 0.543 | |
| F 2 | 9.400 | 9.800 | 0.370 | 0.386 | |
| L | 39.900 | 40.300 | 1.571 | 1.587 | |
| L1 | 23.200 | 23.600 | 0.913 | 0.929 | |
| L 2 | 20.300 | 20.600 | 0.799 | 0.811 | |
| Ф | 6.900 | 7.100 | 0.272 | 0.280 | |
| G | 5.150 | 5.550 | 0.203 | 0.219 | |
| е | 5.450 |) TYP | 0.215 TYP | | |
| Н | 5.000 REF | | 0.197 REF | | |
| h | 0.000 | 0.300 | 0.000 | 0.012 | |



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